

semiconductor material provided with faces having had removed from part of them by abrasion a depth of material.

By contrast, Götzenbrucker describes a method for manufacturing a silicon semiconductor component that includes the steps of preparing a passivating ditch by etching. More specifically, Götzenbrucker teaches (see, for example, Abstract, Claims 1-6, and column 7, line 37 - column 9, line 4) first and second etching steps, including first and second etching masks, to create passivating ditches. The use of the first and second etching steps to create the passivating ditches is believed to be fundamental to the invention of Götzenbrucker, and thus Götzenbrucker is believed to teach away from faces having removed from part of them by abrasion a depth of material, as defined in claim 1.

In the present invention, the use of abrasion to remove a depth of material from faces to expose a junction between regions, in combination with use of a rim at a perimeter, allows among other benefits more easily containable stress in a silicon semiconductor material when shaping beveled surfaces. Applicant respectfully submits that the etching techniques taught in Götzenbrucker do not suggest the abrasion formation defined in claim 1.

Additionally, Applicant respectfully submits that the defined structural feature of faces having removed from part of them by abrasion a depth of material is not disclosed or suggested by the structure of Götzenbrucker, at least because of the use of etching in Götzenbrucker is believed to produce a different structure than that formed by abrasion.

For at least these reasons, Applicant respectfully submits that claim 1 is allowable over the references of record, including Götzenbrucker. Claims 2-3 and 7-11, having at least the features of claim 1, plus additional features, are believed to be allowable for at least the reasons stated above as applied to claim 1, plus additional reasons. Applicant thus respectfully requests reconsideration and withdrawal of the rejection.

Claims 4 and 5 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Götzenbrucker. Applicant respectfully traverses the rejection for at least the reasons stated above as applied to independent claim 1, from which claims 4 and 5 depend, plus additional reasons. Applicant thus respectfully requests reconsideration and withdrawal of the rejection.

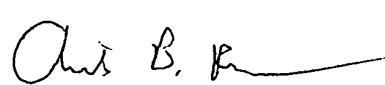
Claim 6 stands rejected under 35 U.S.C. §103(a) as being unpatentable over Götzenbrucker in view of Driscoll. Applicant respectfully traverses the rejection for at least the reasons stated above as applied to independent claim 1 (from which claim 6 depends) regarding Götzenbrucker, and for at least the additional reason that it is believed Götzenbrucker and Driscoll could not be combined to render obvious the subject matter defined in claim 6. Applicant thus respectfully requests reconsideration and withdrawal of the rejection.

For the foregoing reasons, Applicant believes that this case is in condition for allowance, which is respectfully requested. The Examiner should call Applicant's attorney if an interview would expedite prosecution.

Respectfully submitted,

GREER, BURNS & CRAIN, LTD.

By



Arik B. Ranson
Registration No. 43,874

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300 S. Wacker Drive - Suite 2500
Chicago, Illinois 60606-6501
Telephone: (312) 360-0080
Facsimile: (312) 360-9315
Customer No. 24978